



# STE07DE220

Hybrid emitter switched bipolar transistor  
 ESBT® 2200V - 7A - 0.07 Ω power module

Preliminary Data

## Features

Table 1.

$V_{CS(ON)}$	$I_C$	$R_{CS(ON)}$
0.5V	7A	0.07 Ω

- High voltage / high current cascode configuration
- Ultra low equivalent on resistance
- Very fast-switch, up to 150 kHz
- Ultra low  $C_{ISS}$
- Low dynamic  $V_{CS(ON)}$

## Applications

- Industrial converters
- Welding

## Description

The STE07DE220 is manufactured in a hybrid structure, using dedicated high voltage Bipolar and low voltage MOSFET technologies, aimed to providing the best performance in ESBT topology. The STE07DE220 is designed for use in industrial mains flyback converters and/or special applications.

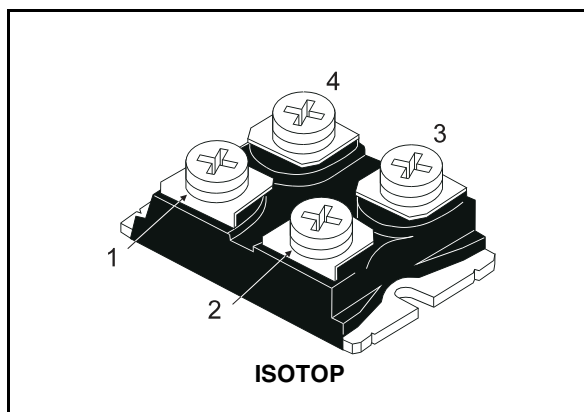


Figure 1. Internal schematic diagrams

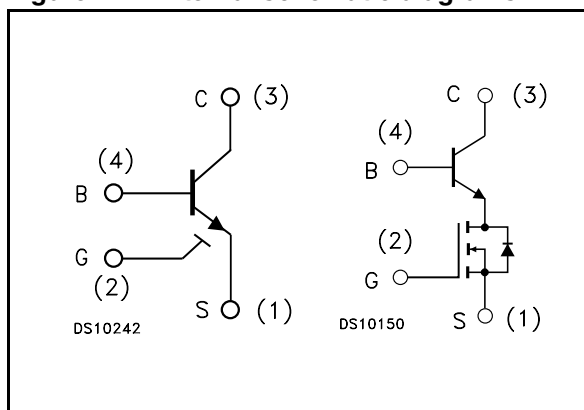


Table 2. Device summary

Order code	Marking	Package	Packaging
STE07DE220	E07DE220	ISOTOP	Tube

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage ( $V_{BS} = V_{GS} = 0$ )	2200	V
$V_{BS(OS)}$	Base-source voltage ( $I_C = 0, V_{GS} = 0$ )	40	V
$V_{SB(OS)}$	Source-base voltage ( $I_C = 0, V_{GS} = 0$ )	10	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_C$	Collector current	7	A
$I_{CM}$	Collector peak current ( $t_P < 5$ ms)	14	A
$I_B$	Base current	7	A
$I_{BM}$	Base peak current ( $t_P < 1$ ms)	14	A
$P_{tot}$	Total dissipation at $T_C \leq 25$ °C	220	W
$T_{stg}$	Storage temperature	-40 to 150	°C
$T_J$	Max. operating junction temperature	125	°C
$V_{ISO}$	Insulation withstand voltage (AC-RMS) from all four leads to external heatsink	2500	V

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.45	°C/W

## 2 Electrical characteristics

( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Electrical characteristics**

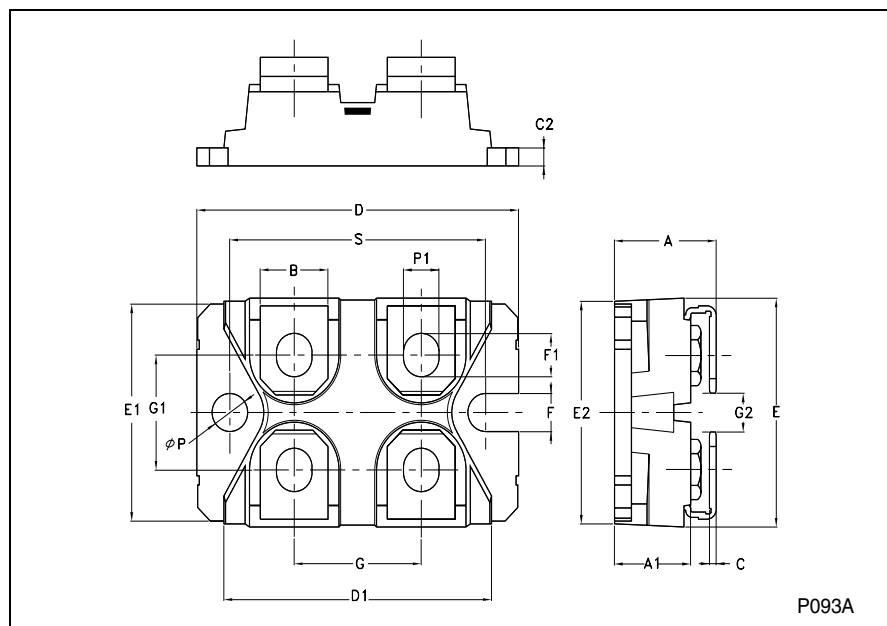
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CS(SS)}}$	Collector-source current ( $V_{\text{BS}} = V_{\text{GS}} = 0$ )	$V_{\text{CS}} = 2200 \text{ V}$			100	$\mu\text{A}$
$I_{\text{BS(OS)}}$	Base-source current ( $I_{\text{C}} = 0, V_{\text{GS}} = 0$ )	$V_{\text{BS}} = 40 \text{ V}$			10	$\mu\text{A}$
$I_{\text{SB(OS)}}$	Source-base current ( $I_{\text{C}} = 0, V_{\text{GS}} = 0$ )	$V_{\text{SB}} = 9 \text{ V}$			100	$\mu\text{A}$
$I_{\text{GS(OS)}}$	Gate-source leakage ( $V_{\text{BS}} = 0$ )	$V_{\text{GS}} = \pm 20 \text{ V}$			500	nA
$V_{\text{CS(ON)}}$	Collector-source ON voltage	$V_{\text{GS}} = 10 \text{ V } I_{\text{C}} = 7 \text{ A } I_{\text{B}} = 1.4 \text{ A}$ $V_{\text{GS}} = 10 \text{ V } I_{\text{C}} = 3.5 \text{ A } I_{\text{B}} = 0.35 \text{ A}$		0.5 0.4		V V
$h_{\text{FE}}$	DC current gain	$V_{\text{GS}} = 10 \text{ V } V_{\text{CS}} = 1 \text{ V } I_{\text{C}} = 7 \text{ A}$ $V_{\text{GS}} = 10 \text{ V } V_{\text{CS}} = 1 \text{ V } I_{\text{C}} = 3.5 \text{ A}$		9 15		
$V_{\text{BS(ON)}}$	Base-source ON voltage	$V_{\text{GS}} = 10 \text{ V } I_{\text{C}} = 7 \text{ A } I_{\text{B}} = 1.4 \text{ A}$ $V_{\text{GS}} = 10 \text{ V } I_{\text{C}} = 3.5 \text{ A } I_{\text{B}} = 0.35 \text{ A}$		1 0.8		V V
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{BS}} = V_{\text{GS}} \quad I_{\text{B}} = 250 \mu\text{A}$	3	3.7	4.5	V
$C_{\text{iss}}$	Input capacitance ( $V_{\text{GS}} = V_{\text{CB}} = 0$ )	$V_{\text{CS}} = 25 \text{ V } f = 1 \text{ MHz}$		t.b.d.		pF
$Q_{\text{GS(tot)}}$	Gate-source charge ( $V_{\text{CB}} = 0$ )	$V_{\text{CS}} = 25 \text{ V } V_{\text{GS}} = 10 \text{ V}$ $I_{\text{C}} = 7 \text{ A}$		t.b.d.		nC
$t_{\text{s}}$ $t_{\text{f}}$	Inductive load Storage time Fall time	$V_{\text{GS}} = 10 \text{ V} \quad R_{\text{G}} = 47 \Omega$ $V_{\text{Clamp}} = 1760 \text{ V} \quad t_{\text{p}} = 4 \mu\text{s}$ $I_{\text{C}} = 3.5 \text{ A} \quad I_{\text{B}} = 0.7 \text{ A}$		t.b.d. t.b.d.		ns ns
$t_{\text{s}}$ $t_{\text{f}}$	Inductive load Storage time Fall time	$V_{\text{GS}} = 10 \text{ V} \quad R_{\text{G}} = 47 \Omega$ $V_{\text{Clamp}} = 1760 \text{ V} \quad t_{\text{p}} = 4 \mu\text{s}$ $I_{\text{C}} = 3.5 \text{ A} \quad I_{\text{B}} = 0.35 \text{ A}$		t.b.d. t.b.d.		ns ns

### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**ISOTOP MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.465		0.480
A1	8.9		9.1	0.350		0.358
B	7.8		8.2	0.307		0.322
C	0.75		0.85	0.029		0.033
C2	1.95		2.05	0.076		0.080
D	37.8		38.2	1.488		1.503
D1	31.5		31.7	1.240		1.248
E	25.15		25.5	0.990		1.003
E1	23.85		24.15	0.938		0.950
E2		24.8			0.976	
G	14.9		15.1	0.586		0.594
G1	12.6		12.8	0.496		0.503
G2	3.5		4.3	0.137		1.169
F	4.1		4.3	0.161		0.169
F1	4.6		5	0.181		0.196
P	4		4.3	0.157		0.169
P1	4		4.4	0.157		0.173
S	30.1		30.3	1.185		1.193



## 4 Revision history

**Table 5. Document revision history**

Date	Revision	Changes
20-May-2008	1	First release.

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